

a second nitride based semiconductor layer, formed on said first nitride based semiconductor layer in said striped opening, including a second conductivity type cladding layer and containing at least one of boron, aluminum, gallium, indium and thallium, wherein

said current blocking layer includes a multilayer structure of at least one first layer of a nitride based semiconductor containing at least one of aluminum and boron and at least one second layer of a nitride based semiconductor containing indium and having a smaller band gap than said first layer.

2. (Amended) The semiconductor laser device according to claim 1, wherein

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and
said at least one first layer of a nitride based semiconductor has a larger aluminum composition ratio than that of said at least one second layer of a nitride based semiconductor or a larger boron composition ratio than that of said at least one second layer of a nitride based semiconductor, and

said at least one second layer of a nitride based semiconductor has a larger indium composition ratio than that of said at least one first layer of a nitride based semiconductor.

3. (Amended) The semiconductor laser device according to claim 1, wherein

said first nitride based semiconductor layer further includes a second conductivity type cladding layer provided between said active layer and a second conductivity type second conductivity type cladding layer in said second nitride based semiconductor layer.
